# MSKSEMI 美森科













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## OPA376AIDBVR-MS/OPA2376AIDR-MS

**Product specification** 





## Ultra Low Noise Rail-to-Rail I/O CMOS Precision OPERATIONAL AMPLIFIERS

## **GENERAL DESCRIPTION**

The OPA376 family represents a newgeneration of low-noise operational amplifiers,offering outstanding dc precision and acperformance.Rai-to-Rail input and output,lowoffset (2 $\mu$ V),low noise(6nVNHz),quiescentcurrent of 600  $\mu$ A,and a 6-MHz band widthmake this part very attractive for a variety of precision and portable applications

In addition, this device has a reasonably widesup ply range(2V to 5.5V) with excellent PSRR making it attractive for applications that rundirectly from batteries without regulation.

The OPA376AIDBVR-MS(single), OPA2376AIDR-M S(dual) families of operational amplifiers are specified for operation from -25°C to +125°C.

### **FEATURES**

- Input Offset Voltage:2µV (Typical)
- Zero Drift:0.03µV/C (Typical)
- Ultra Low Noise:6nV/VHz at 1kHz
- Supply Range:2V to 5.5V
- Gain Bandwidth:6 MHz
- Slew rate:5V/us
- Quiescent current:600µA (Vs=5V)
- Rail-to-Rail Input and Output
- Micro size Packages:
  OPA376AIDBVR-MS:SOT-23-5
  OPA2376AIDR-MS:SOP-8

## **APPLICATIONS**

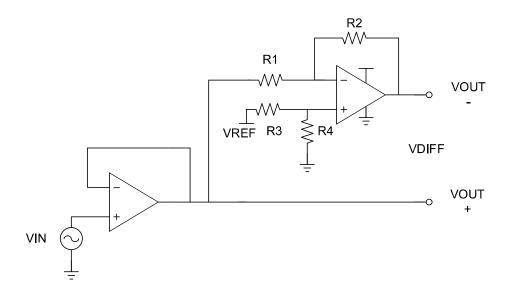
- ADC Buffer
- Audio Equipment
- Medical Instrumentation
- Handheld Test Equipment
- Active Filtering
- Sensor Signal Conditioning

### **Reference News**

MODEL	Op Temp(℃)	PACKAGE OUTLINE		Marking	Minimum packaging (PCS)
OPA376AIDBVR-MS	-25℃~125℃	SOT-23-5		BUQ	3000
OPA2376AIDR-MS	-25℃~125℃	SOP-8		MSKSEMI OPA2376 ●	2500

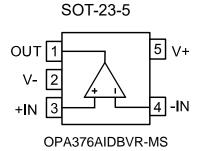


## **TYPICAL APPLICATION**



**Figure 1.Typical Application** 

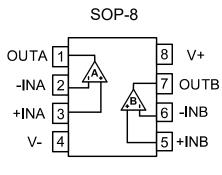
## Pin Configuration and Functions (Top View) Pin Description



PIN		I/0	DESCRIPTION	
NAME	Number	1/0	DESCRIT TION	
+IN	3	I	Positive (noninverting)input	
-IN	4	I	Negative(inverting)input	
OUT	1	0	Output	
V-	2	_	Positive(highest)power supply	
V+	5	_	Negative(lowest)power supply	



## Pin Configuration and Functions (Top View) Pin Description



OPA2376AIDR-MS

PIN		1/0	DESCRIPTION	
NAME	Number	1/0	DESCRIT I TON	
+INA	3		Noninverting input, channel A	
+INB	5		Noninverting input, channel B	
-INA	2		Inverting input, channel A	
-INB	6		Inverting input, channel B	
OUTA	1	0	Output, channel A	
OUTB	7	0	Output, channel B	
V-	4		Negative (lowest)power supply	
V+	8		Positive (highest) power supply	



## **SPECIFICATIONS**

## **Absolute Maximum Ratings**(1)

		MIN	MAX	UNIT
	Supply Voltage		6	V
Voltage	Signal Input Terminals Voltage <sup>(2)</sup>	(V-) - 0.5	(V+) + 0.5	V
	Signal Input Terminals Voltage <sup>(3)</sup>	(V-) - 0.5	(V+) + 0.5	V
	Signal Input Terminals Current <sup>(2)</sup>	-10	10	mA
Current	Signal output Terminals Current <sup>(3)</sup>	<b>-</b> 200	200	mA
	Output Short-Circuit <sup>(4)</sup>	Continuous		
	Operating Temperature Range	<b>-</b> 25	125	°C
$\theta_{JA}$	Storage Temperature Range	<b>-</b> 65	150	°C
	Junction Temperature	<b>-</b> 40	150	°C

<sup>(1)</sup> Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

- (2) Input terminals are diode clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current limited to 10mA or less.
- (3) Output terminals are diode-clamped to the power-supply rails. Output signals that can swing more than 0.5V beyond the supply rails should be current-limited to ±200mA or less.
- (4) Short-circuit to ground, one amplifier per package.

## **ESD Ratings**

			VALUE	UNIT
		Human-Body Model (HBM)	±4000	V
$V_{(ESD)}$	Electrostatic discharge	Charged-Device Model (CDM)	±500	V
		Machine Model	100	V

## **Recommended Operating Conditions**

		MIN	MAX	UNIT
Supply voltage,	Single-supply	2	5.5	V
Vs= (V+) - (V-)	Dual-supply	±1	±2.75	V



## **ELECTRICAL CHARACTERISTICS(V<sub>S</sub> = +5V)**

At  $T_A = 25$ °C,  $V_{CM}=V_{OUT}=V_S/2$ , unless otherwise noted.

	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET	VOLTAGE					
Vos	Input Offset Voltage			2	10	μV
dV <sub>OS</sub> /dT	Input Offset Voltage Average Drift	T <sub>A</sub> = <b>-</b> 25°C to 125°C		0.03		μV/°C
INPUT C	URRENT					
<b>I</b> B	Input Bias Current			500		pА
los	Input Offset Current			50		pА
NOISE						
V <sub>N</sub>	Input Voltage Noise	f=0.1Hz to 10Hz		0.3		μV <sub>PP</sub>
e <sub>n</sub>	Input Voltage Noise Density	f=1kHz		6		nV/√Hz
INPUT V	OLTAGE					
V <sub>CM</sub>	Common-Mode Voltage Range		V <sub>S</sub> -0.1		V <sub>S+</sub> +0.1	V
CMRR	Common-Mode Rejection Ratio	V <sub>CM</sub> =0.1V to 4V	110	130		dB
FREQUE	NCY RESPONSE					
GBW	Gain-Bandwidth Product	C <sub>L</sub> =100pF		6		MHz
SR	Slew Rate	G = +1, V <sub>IN</sub> =2V Step		5		V/us
ts	Settling Time to 0.1%	G = +1, V <sub>IN</sub> =2V Step		0.7		us
THD+N	Total Harmonic Distortion +Noise	G=1, $V_O$ =1 $V_{RMS}$ , f=1 $kHz$ , $R_L$ =10 $k\Omega$		0.0004		%
OUTPUT	,		•			
A <sub>V</sub>	Open <b>-</b> Loop Vo <b>l</b> tage Gain	$V_{OUT}$ =0.1V to 4.9V $R_L$ =10k $\Omega$	135	150		dB
V <sub>OH</sub>	High output voltage swing	R <sub>L</sub> =10kΩ		10	20	mV
<b>V</b> OH	Thigh output voltage swilly	R <sub>L</sub> =2kΩ		50	60	mV

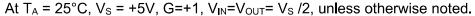


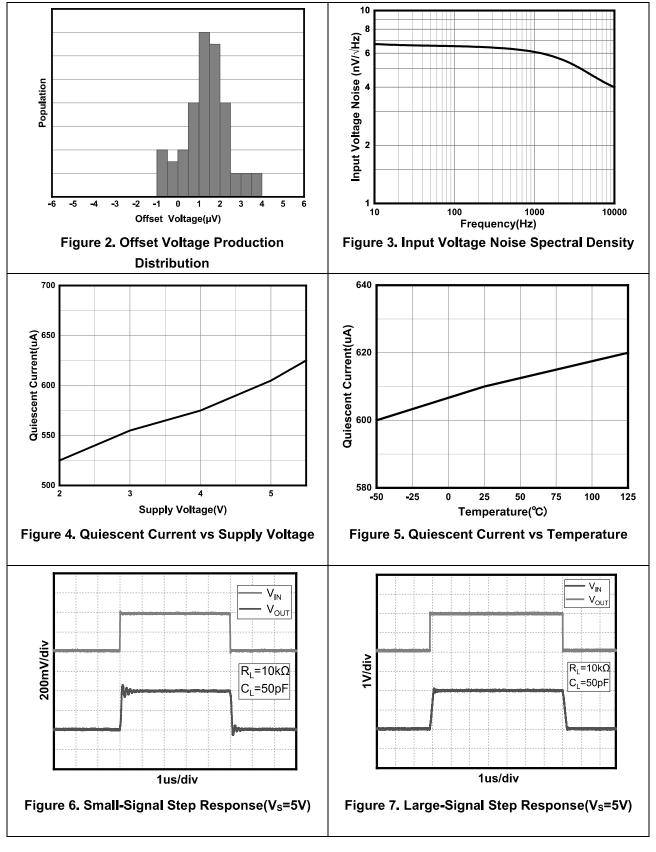
V <sub>OL</sub>	Low output voltage swing	$R_L$ =10k $\Omega$		10	20	mV
		R <sub>L</sub> =2kΩ		35	45	mV
I <sub>sc</sub>	Output Short-Circuit Current	Source current		30		mA
		Sink current		65		mA
C <sub>L</sub> <sup>(1)</sup>	Capacitive Load Drive	G = +1, V <sub>IN</sub> =0.2V Step			560	pF
POWER	SUPPLY					
PSRR	Power-Supply Rejection Ratio	V <sub>S</sub> =1.5V to 5.5V	110	130		dB
Vs	Operating Voltage Range		2		5.5	V
IQ	Quiescent Current/Amplifier	I <sub>O</sub> =0A		600	700	uA

<sup>(1)</sup> Capacitive load drive means that above a given maximum value, the output waveform will oscillate under the step response.



## TYPICAL CHARACTERISTICS

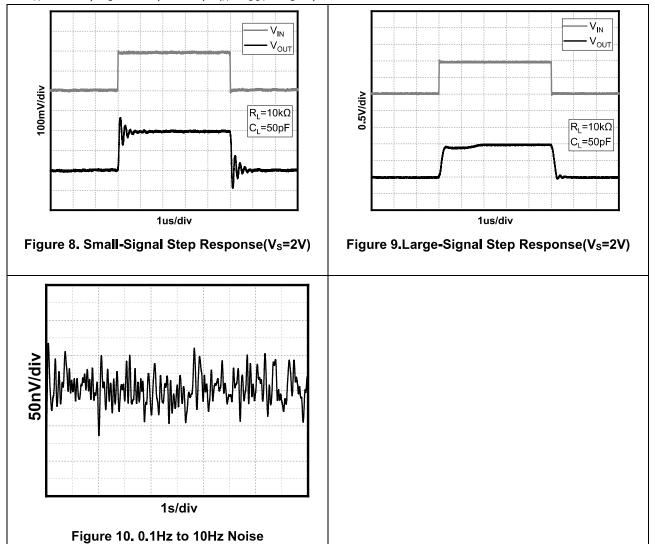






## **TYPICAL CHARACTERISTICS**

At  $T_A = 25$ °C,  $V_S = +5V$ , G=+1,  $V_{IN}=V_{OUT}=V_S/2$ , unless otherwise noted.





## **Detailed Description**

### Oyerview

The OPA376AIDBVR-MS OPA2376AIDR-MS devices are a low noise,unity-gain stable,rai-to-rail precision operational amplifier that operate in a single-supply voltage range of 2V to 5.5V(±1V to±2.75V).A high supply voltage of 6V(absolute maximum)can permanently damage the amplifier.Rail-to-rail input and output wobbles significantly increase the dynamic range,especially in low-supply applications.Good layout practices require that a 0.1uF capacitor be used where it is tightly threaded through the power supply pin.

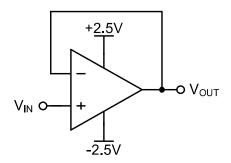
#### **Phase Reversal Protection**

The OPA376AIDBVR-MS OPA2376AIDR-MS devices have internal phase-reversal protection.Many operamps exhibit phase reversal when the input is driven beyond the linear common-mode range. This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The input of the OPA376AIDBVR-MS OPA2376AIDR-MS prevents phase reversal with excessive commonm ode voltage. Instead, the appropriate rail limits the output voltage.

## **Typical Applications**

### 1 Voltage Follower

As shown in Figure 11,the voltage gain is 1. With this circuit, the output voltage Vour is configured to be equal to the input voltage Viw. Due to the high input impedance and low output impedance, the circuit can also stabilize the output voltage, the output voltage expression is



### 2 Inverting Proportional Amplifier

As shown in Figure 12, for a reverse-phase proportional amplifier, the input voltage Vin is amplified by a voltage gain that depends on the ratio of R1 to R2. The output voltage Vour is inversely with the input voltage Vin. The input impedance of the circuit is equal to R1, and the output voltage expression is

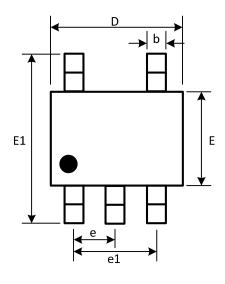
(2)

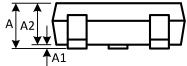
$$V_{OUT} = \frac{R2}{R1} V_{IN}$$



## **PACKAGE DESCRIPTION**

## SOT23-5





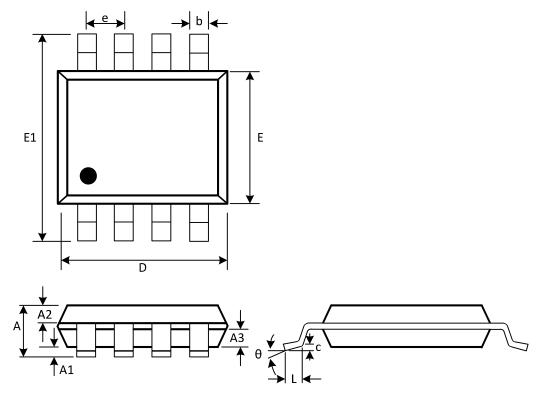


(Unit: mm)

Symbol	Min	Max	
А	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.820	3.020	
e	0.950(BSC)		
e1	1.800	2.000	
E	1.500	1.700	
E1	2.650	2.950	
L	0.300	0.600	
θ	0°	8°	



## SOP-8



(Unit: mm)

Symbol	Min	Max
А	1.300	1.600
A1	0.050	0.200
A2	0.550	0.650
A3	0.550	0.650
b	0.356	0.456
С	0.203	0.233
D	4.800	5.000
е	1.270	(BSC)
E	3.800	4.000
E1	5.800	6.200
L	0.400	0.800
θ	0°	8°



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